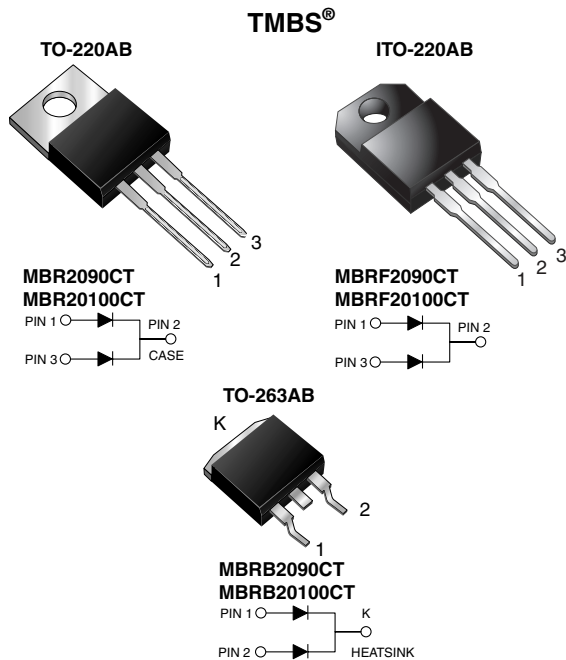




Dual Common-Cathode High-Voltage Schottky Rectifier



FEATURES

- Trench MOS Schottky technology
- Lower power losses, high efficiency
- Low forward voltage drop
- High forward surge capability
- High frequency operation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C (for TO-263AB package)
- Solder dip 260 °C, 40 s (for TO-220AB and ITO-220AB package)
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
 COMPLIANT

TYPICAL APPLICATIONS

For use in high frequency rectifier of switching mode power supplies, freewheeling diodes, dc-to-dc converters or polarity protection application.

MECHANICAL DATA

Case: TO-220AB, ITO-220AB, TO-263AB

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per J-STD-002 and JESD22-B102

E3 suffix for consumer grade, meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS

$I_{F(AV)}$	10 A x 2
V_{RRM}	90 V, 100 V
I_{FSM}	150 A
V_F	0.65 V
$T_J \text{ max.}$	150 °C

MAXIMUM RATINGS ($T_C = 25 \text{ °C}$ unless otherwise noted)

PARAMETER	SYMBOL	MBR2090CT	MBR20100CT	UNIT
Maximum repetitive peak reverse voltage	V_{RRM}	90	100	V
Working peak reverse voltage	V_{RWM}	90	100	V
Maximum DC blocking voltage	V_{DC}	90	100	V
Maximum average forward rectified current at $T_C = 133 \text{ °C}$ total device per diode	$I_{F(AV)}$	20 10		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I_{FSM}	150		A
Peak repetitive reverse current per diode at $t_p = 2 \text{ }\mu\text{s}$, 1 kHz	I_{RRM}	0.5		A
Voltage rate of change (rated V_R)	dV/dt	10 000		V/ μs
Operating junction and storage temperature range	T_J, T_{STG}	- 65 to + 150		°C
Isolation voltage (ITO-220AB only) From terminal to heatsink $t = 1 \text{ min}$	V_{AC}	1500		V



ELECTRICAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	TEST CONDITIONS		SYMBOL	VALUE	UNIT
Maximum instantaneous forward voltage per diode (1)	$I_F = 10\text{ A}$	$T_C = 25\text{ }^\circ\text{C}$	V_F	0.80	V
	$I_F = 10\text{ A}$	$T_C = 125\text{ }^\circ\text{C}$		0.65	
	$I_F = 20\text{ A}$	$T_C = 125\text{ }^\circ\text{C}$		0.75	
Maximum reverse current per diode at working peak reverse voltage (2)		$T_J = 25\text{ }^\circ\text{C}$ $T_J = 100\text{ }^\circ\text{C}$	I_R	100 6.0	μA mA

Notes:

- (1) Pulse test: 300 μs pulse width, 1 % duty cycle
- (2) Pulse test: Pulse width $\leq 40\text{ ms}$

THERMAL CHARACTERISTICS ($T_C = 25\text{ }^\circ\text{C}$ unless otherwise noted)					
PARAMETER	SYMBOL	MBR	MBRF	MBRB	UNIT
Typical thermal resistance per diode	$R_{\theta JA}$ $R_{\theta JC}$	60 2.0	- 3.5	60 2.0	$^\circ\text{C/W}$

ORDERING INFORMATION (Example)					
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE
TO-220AB	MBR20100CT-E3/4W	1.88	4W	50/tube	Tube
ITO-220AB	MBRF20100CT-E3/4W	1.75	4W	50/tube	Tube
TO-263AB	MBRB20100CT-E3/4W	1.38	4W	50/tube	Tube
TO-263AB	MBRB20100CT-E3/8W	1.38	8W	800/reel	Tape and reel

RATINGS AND CHARACTERISTICS CURVES

($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

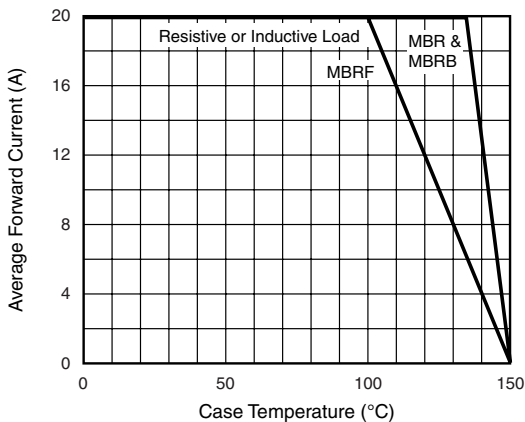


Figure 1. Forward Current Derating Curve

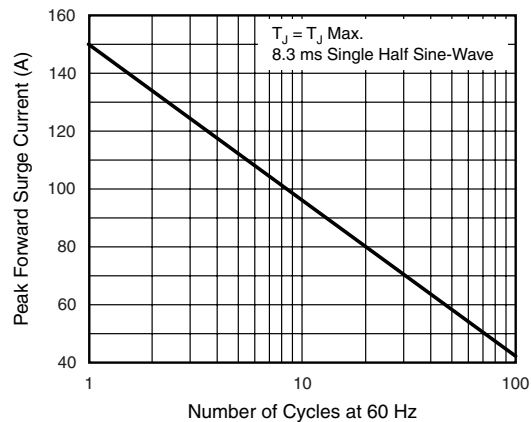


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode

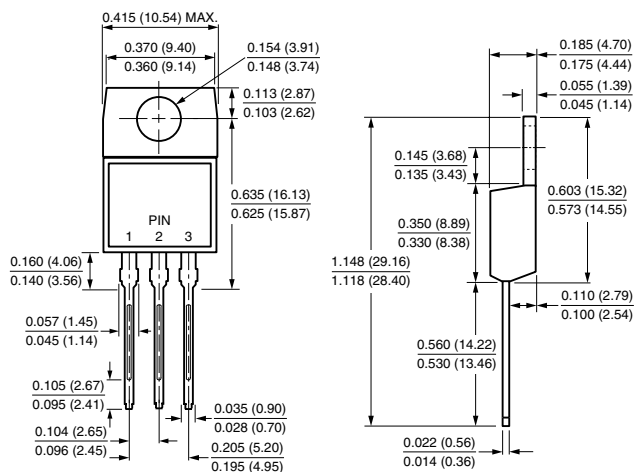
New Product MBR(F,B)2090CT & MBR(F,B)20100CT



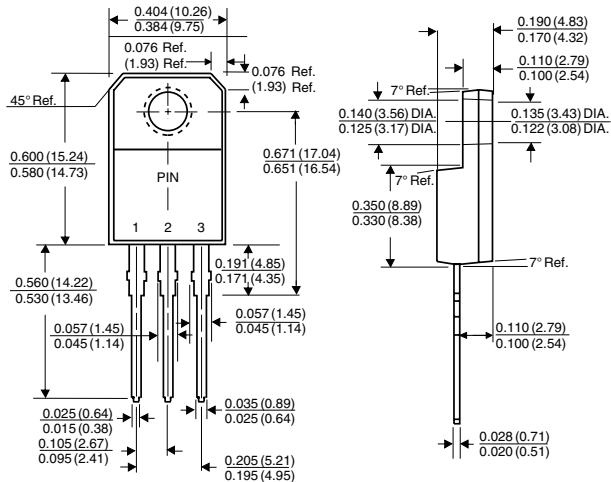
Vishay General Semiconductor

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)

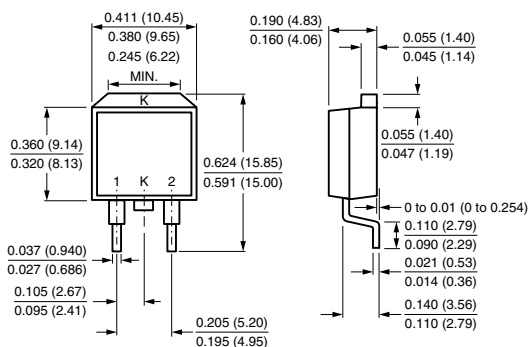
TO-220AB



ITO-220AB



TO-263AB



Mounting Pad Layout

